NANOTECH

Process

(PE)CVD, Metal, ALD, Etcher

Application

Endpoint detection, Process fault

Features & Benefits

- In-Situ Process Monitor
- Control the process accurately and stably
- Improve production yield-rate
- Cope with the change of process promptly

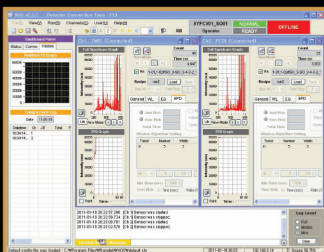
2014 Product Catalog VOL.1

Optical Emission Spectrometer OES

Model OPTI Series

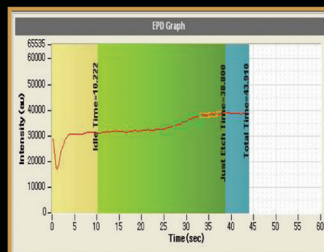
Screen Overview

- 3 Panels (Dashboard, Works pace, Log panel)
- 2Bars (Menu&tool, Status bar)
- Various multi channel view



EPD Function

- Endpoint detection by EPD algorithm
- Auto start by EPD start signal
- Sending EPD signal and time information to equipment

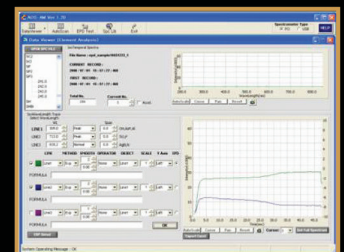


AOS

- Confirmation of EPD algorithm by window method
- Initial dead time setting
- Over etch time setting (time, percent)

AOS-AM(Data Viewer)

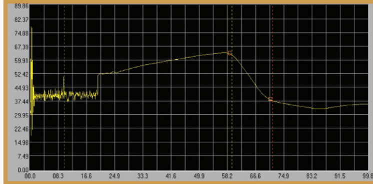
- Single File Analysis
- Multi File Analysis
- Element Analysis
- Export data to .txt or .csv file



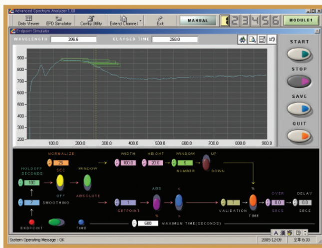
Optical Emission Spectrometer **OES**

Model AEGIS Series

WAFER PR ASHING & AL ETCHING



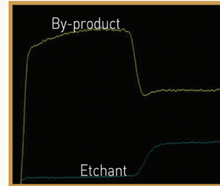
_ PR ashing (CO peak wavelength)
_ Single wafer type, Mass run (Samsung, Hynix)
_ EPD NEM10-VM



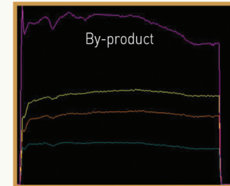
_ Al etching (Al peak wavelength)
_ Wafer #10 batch type, Mass run (Fairchild)
_ EPD NEC-410

α - SI LCD PROCESS

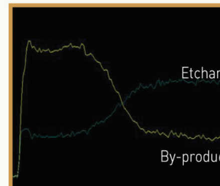
_ Endpoint detection at the following processes



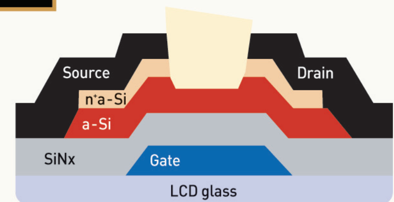
_ Active



_ Passivation



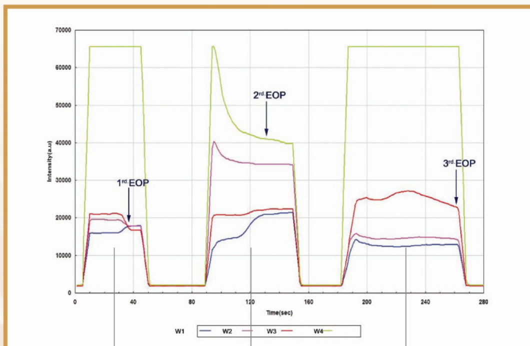
_ PR strip



Single layer
FPD(LCD)
Multi layer
Semi

WAFER MULTI-LAYER ETCHING

CO CF2 SiF f (CF2, SiF)



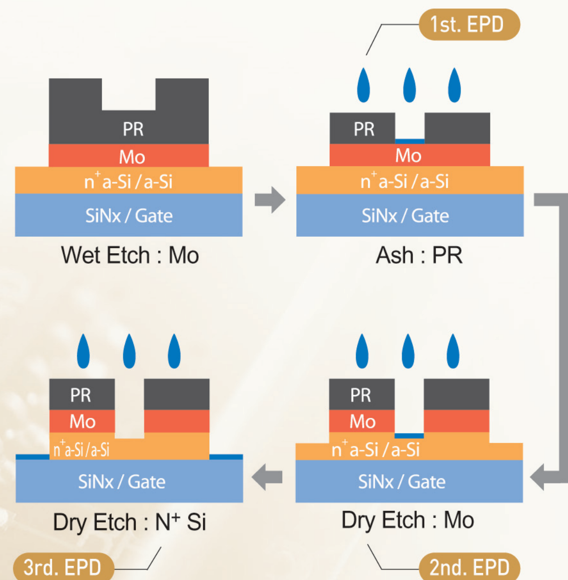
3rd. Step : PR(O2/N2 gas)

2nd. Step : Si-compound(CF4/He gas)

1st. Step : PR(O2/N2 gas)

_ Endpoint at each step is clearly and accurately detected.

LCD 4-MASK MULTI-STEP



NANOTECH